

N-channel 600 V, 0.45 Ω typ., 13.5 A SuperMESH™
Power MOSFETs in I²PAK, TO-220 and TO-247 packages

Datasheet - obsolete product

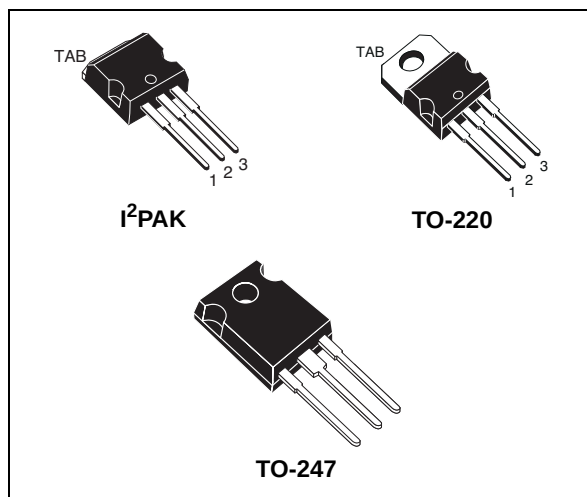
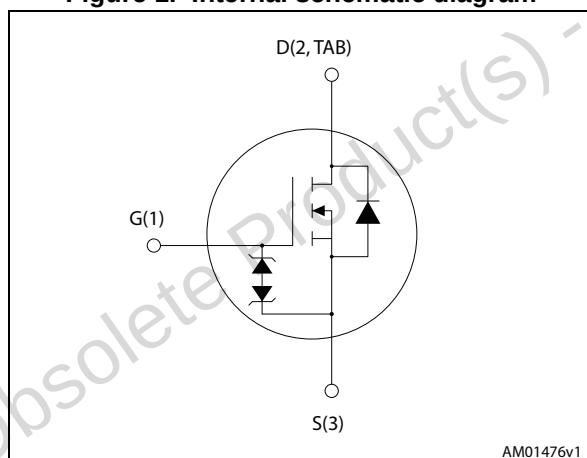


Figure 1. Internal schematic diagram



Features

Order codes	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STB14NK60Z-1	600 V	0.5 Ω	13.5 A	160 W
STP14NK60Z				
STW14NK60Z				

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Zener-protected Power MOSFETs developed using STMicroelectronics' SuperMESH™ technology, achieved through optimization of ST's well established strip-based PowerMESH™ layout. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB14NK60Z-1	B14NK60Z	I ² PAK	Tube
STP14NK60Z	P14NK60Z	TO-220	
STW14NK60Z	W14NK60Z	TO-247	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)	600	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	13.5	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	8.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	54	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	160	W
	Derating factor	1.28	W/ $^\circ\text{C}$
ESD	Gate-source human body model ($R = 1.5\text{ k}\Omega$, $C = 100\text{ pF}$)	4	kV
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 13.5\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq T_{JMAX}$.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.78	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_{Jmax})	12	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	300	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 600 \text{ V}$			1	μA
		$V_{DS} = 600 \text{ V}$, $T_C=125^{\circ}\text{C}$			50	μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 30 \text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100 \mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$, $I_D = 6 \text{ A}$		0.45	0.5	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$, $V_{GS} = 0$	-	2220	-	pF
C_{oss}	Output capacitance		-	240	-	pF
C_{rss}	Reverse transfer capacitance		-	57	-	pF
$C_{oss \text{ eq}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0 \text{ V to } 480 \text{ V}$	-	122	-	pF
Q_g	Total gate charge	$V_{DD} = 480 \text{ V}$, $I_D = 12 \text{ A}$ $V_{GS} = 10 \text{ V}$	-	75	-	nC
Q_{gs}	Gate-source charge		-	13.2	-	nC
Q_{gd}	Gate-drain charge		-	38.6	-	nC

1. $C_{oss \text{ eq}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=300\text{ V}$, $I_D=6\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 17)	-	26	-	ns
t_r	Rise time		-	18	-	ns
$t_{d(off)}$	Turn-off delay time		-	62	-	ns
t_f	Fall time		-	13	-	ns
$t_{r(Voff)}$	Off-voltage rise time	$V_{DD}=480\text{ V}$, $I_D=12\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 19)	-	12	-	ns
t_f	Fall time		-	9.5	-	ns
t_c	Cross-over time		-	22	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		12	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		48	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=12\text{ A}$, $V_{GS}=0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD}=12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD}=50\text{ V}$	-	490		ns
Q_{rr}	Reverse recovery charge		-	4.7		μC
I_{RRM}	Reverse recovery current		-	19.3		A
t_{rr}	Reverse recovery time	$I_{SD}=12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD}=50\text{ V}$, $T_j=150\text{ }^\circ\text{C}$	-	664		ns
Q_{rr}	Reverse recovery charge		-	6.8		μC
I_{RRM}	Reverse recovery current		-	20.5		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 9. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{mA}$, $I_D=0$	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance the device's ESD capability. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for I²PAK and TO-220

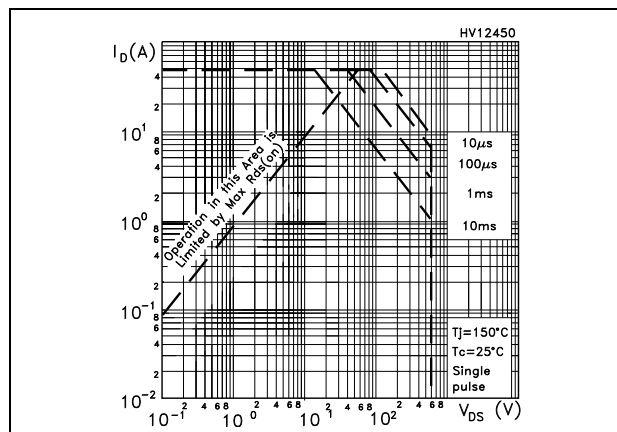


Figure 3. Thermal impedance for I²PAK and TO-220

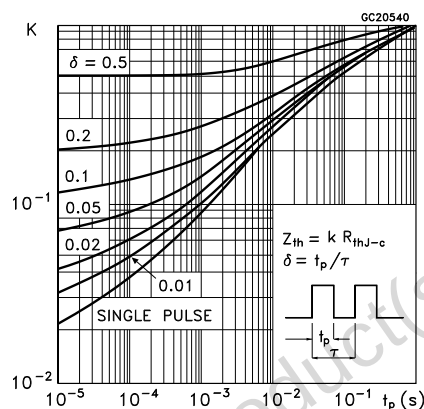


Figure 4. Safe operating area for TO-247

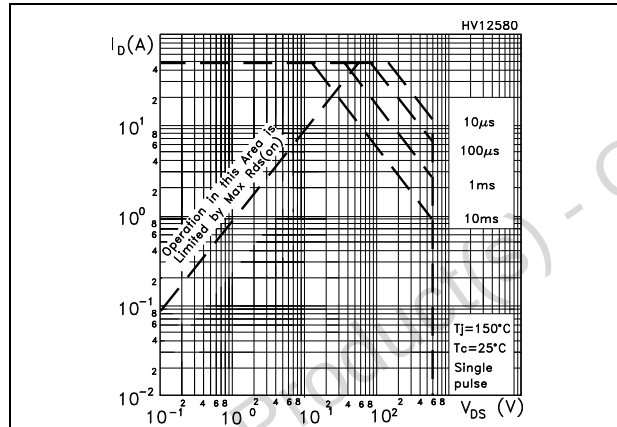


Figure 5. Thermal impedance for TO-247

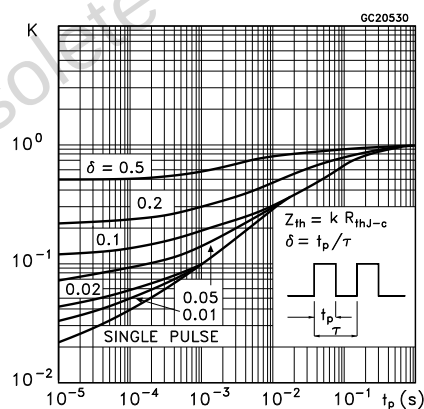


Figure 6. Output characteristics

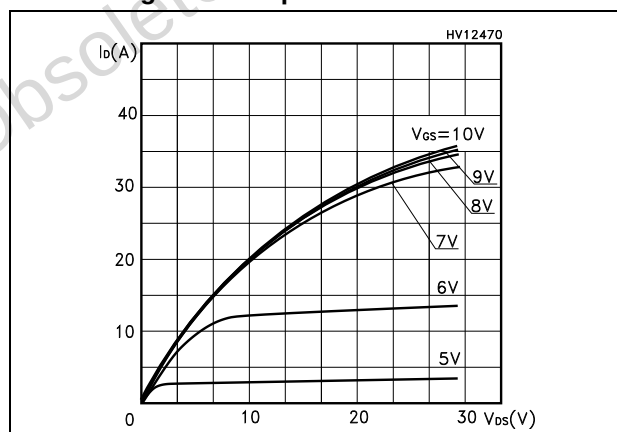


Figure 7. Transfer characteristics

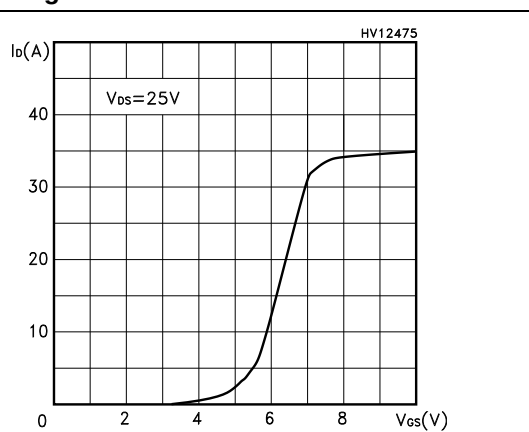


Figure 8. Transconductance

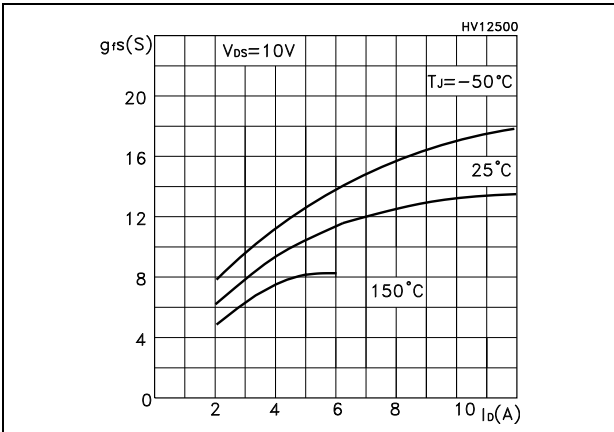


Figure 9. Static drain-source on-resistance

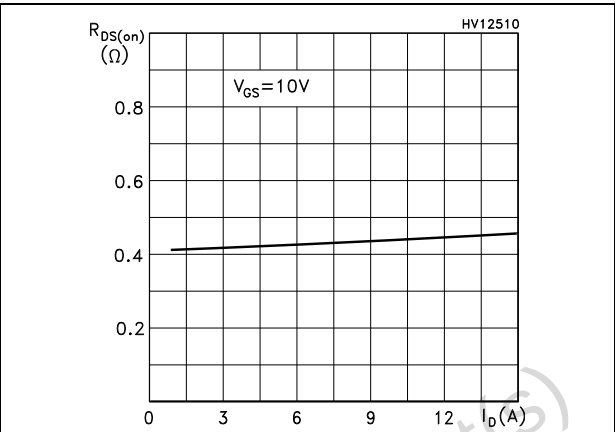


Figure 10. Gate charge vs gate-source voltage

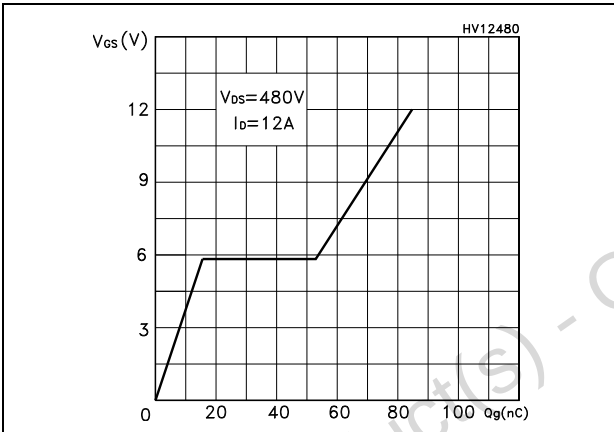


Figure 11. Capacitance variations

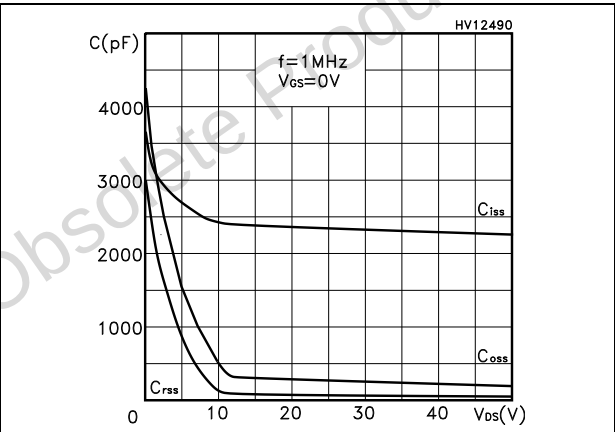


Figure 12. Normalized gate threshold voltage vs temperature

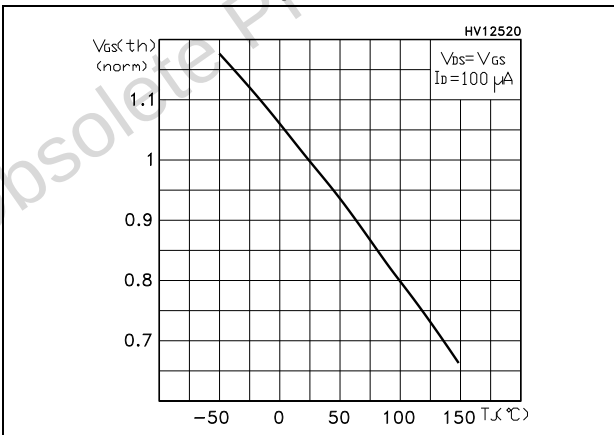


Figure 13. Normalized on-resistance vs temperature

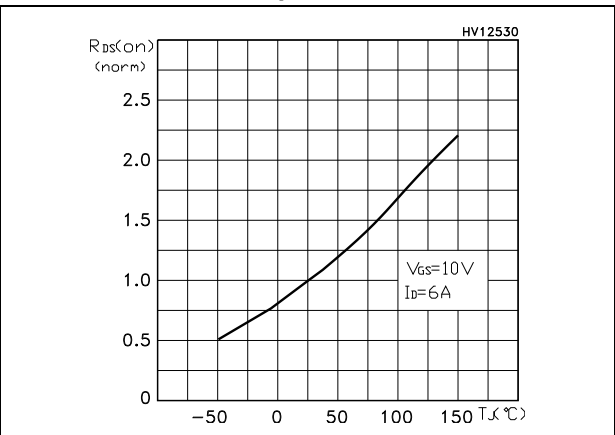


Figure 14. Source-drain diode forward characteristics

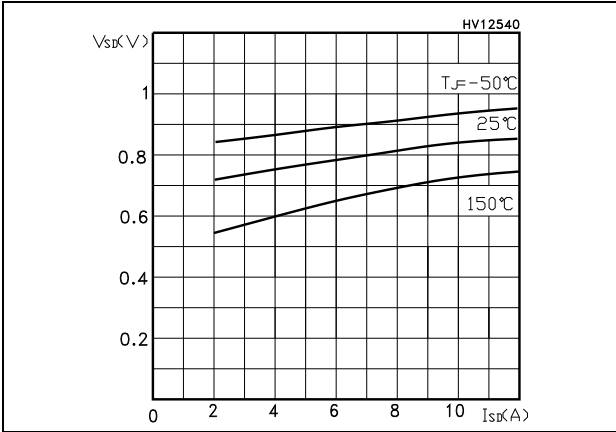


Figure 15. Normalized $V_{(BR)DSS}$ vs temperature

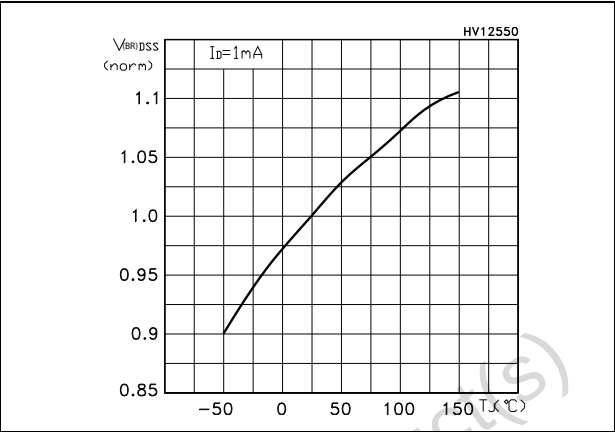
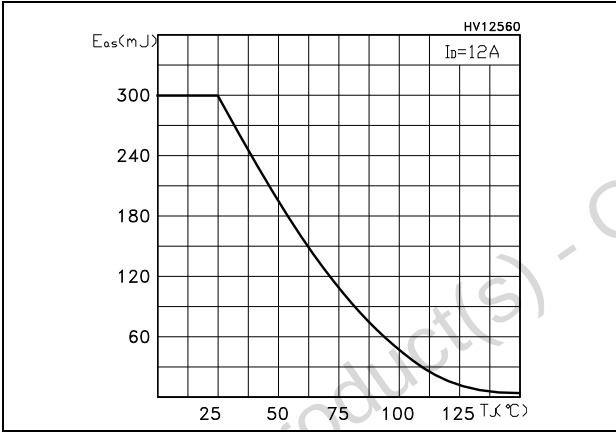
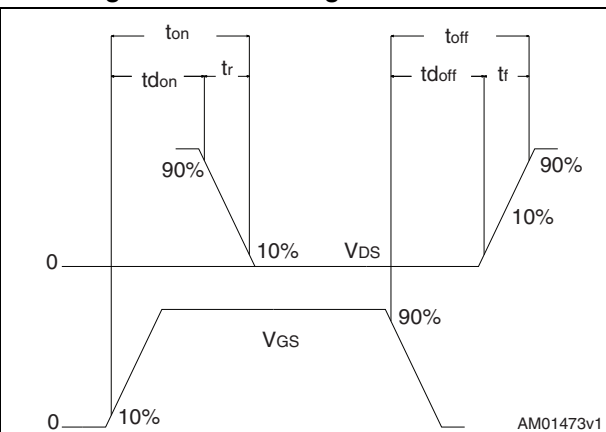
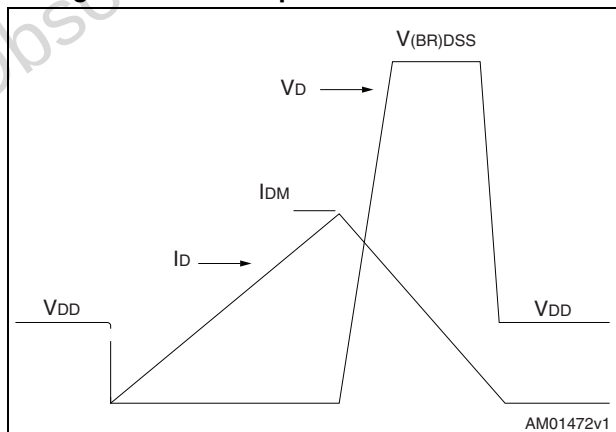
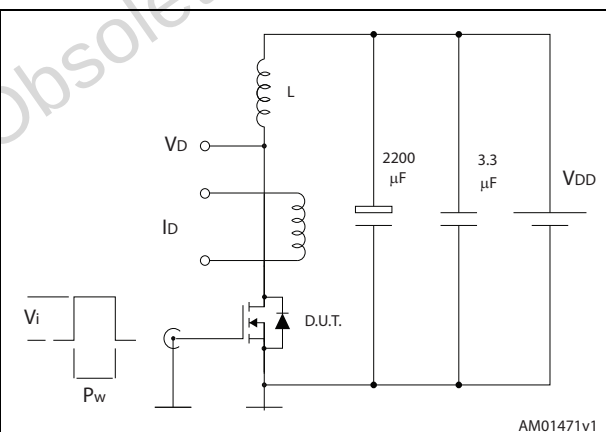
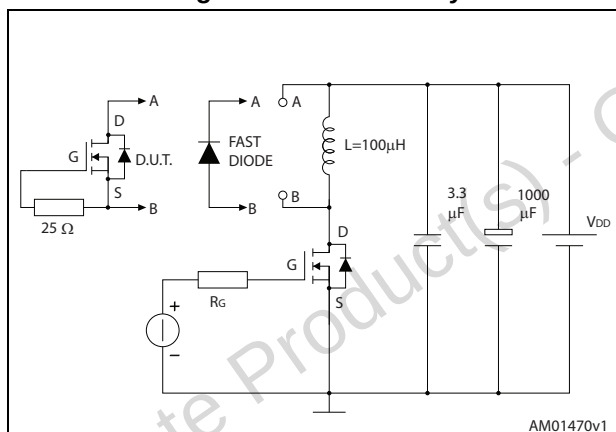
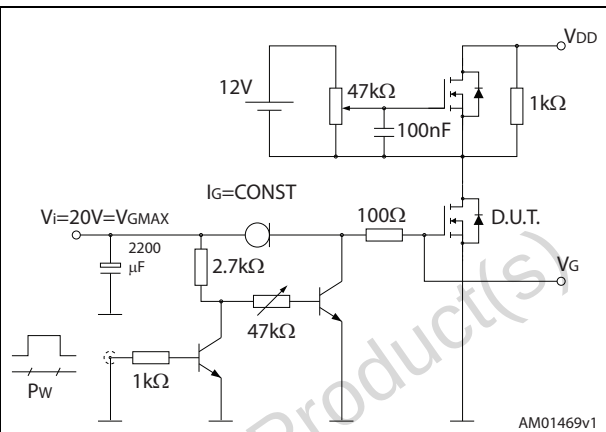
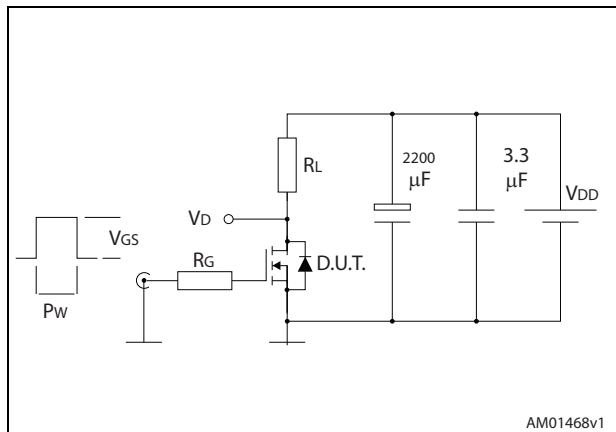


Figure 16. Maximum avalanche energy vs temperature





4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Obsolete Product(s) - Obsolete Product(s)

4.1 I²PAK, STB14NK60Z

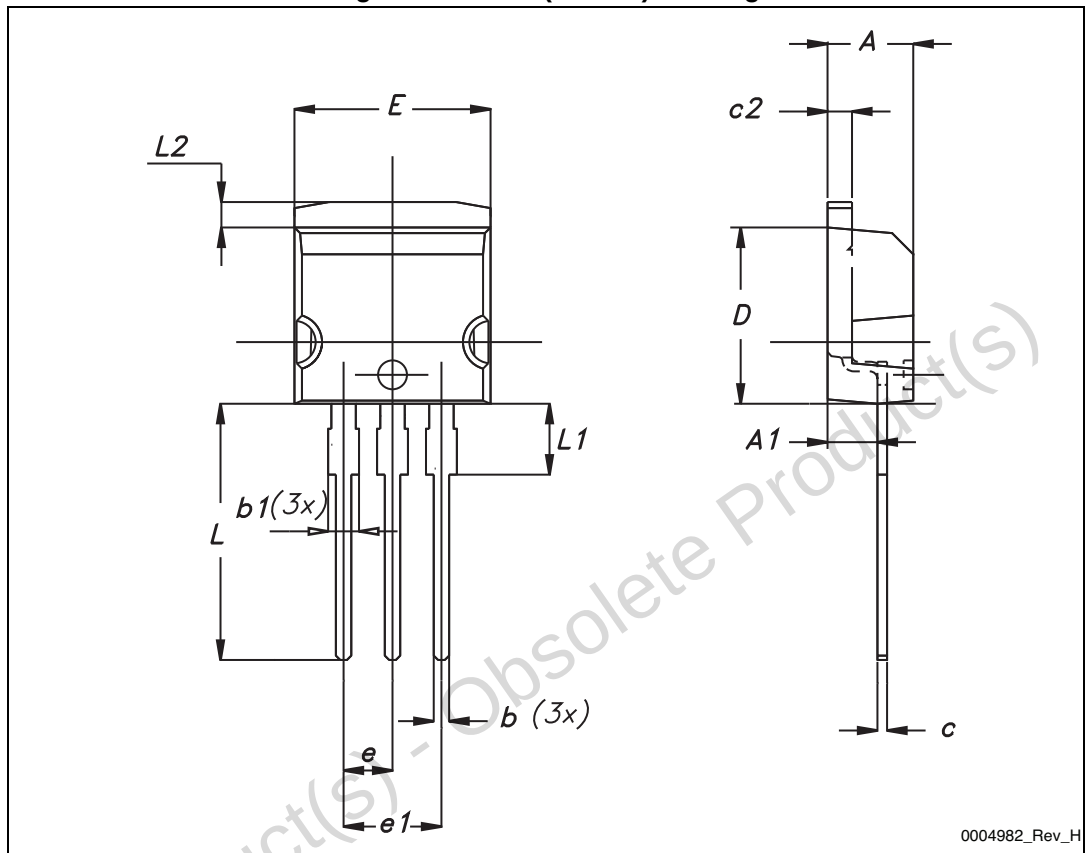
Figure 23. I²PAK (TO-262) drawing

Table 10. I²PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

4.2 TO-220, STP14NK60Z

Figure 24. TO-220 type A drawing

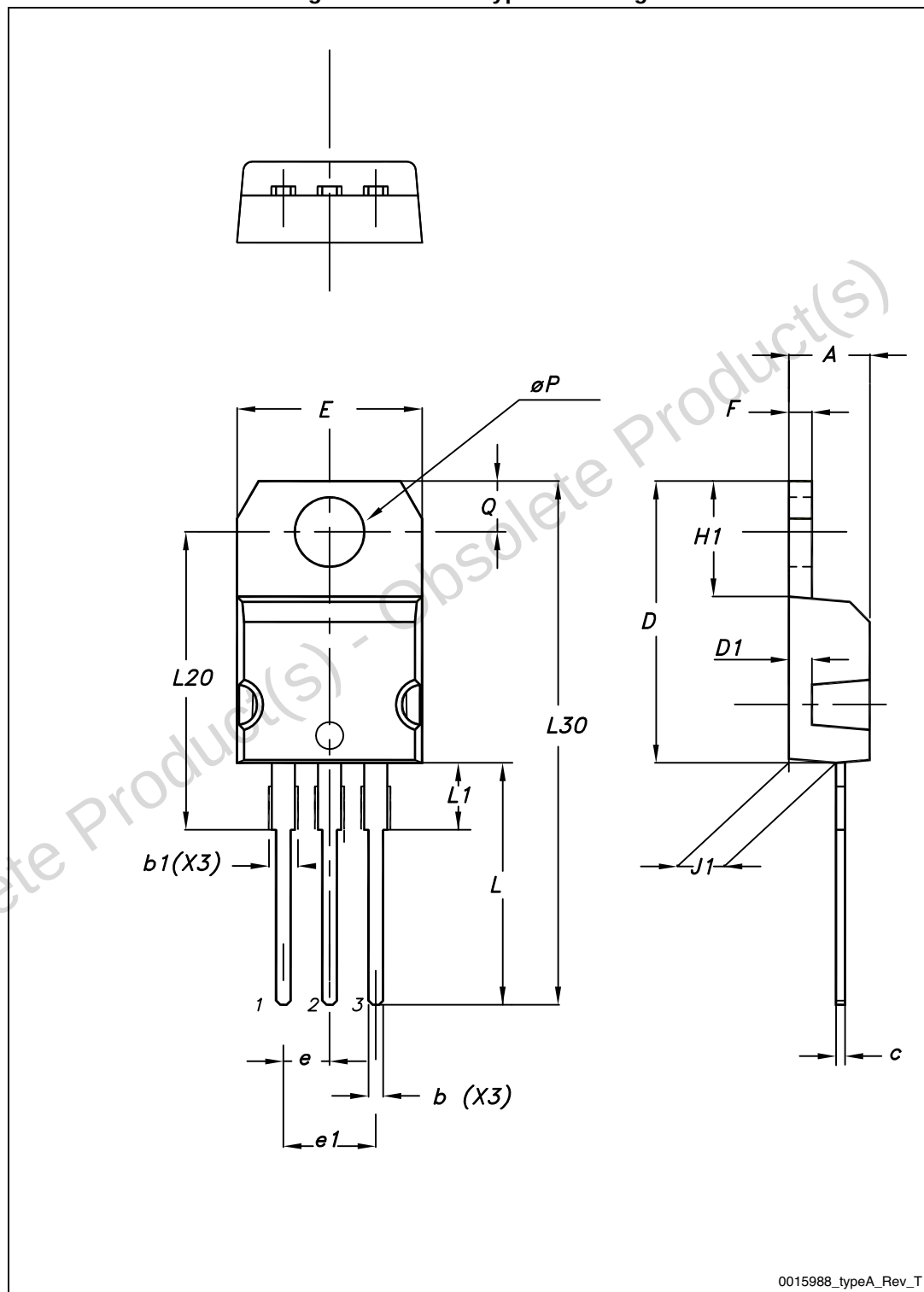


Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

4.3 TO-247, STW14NK60Z

Figure 25. TO-247 drawing

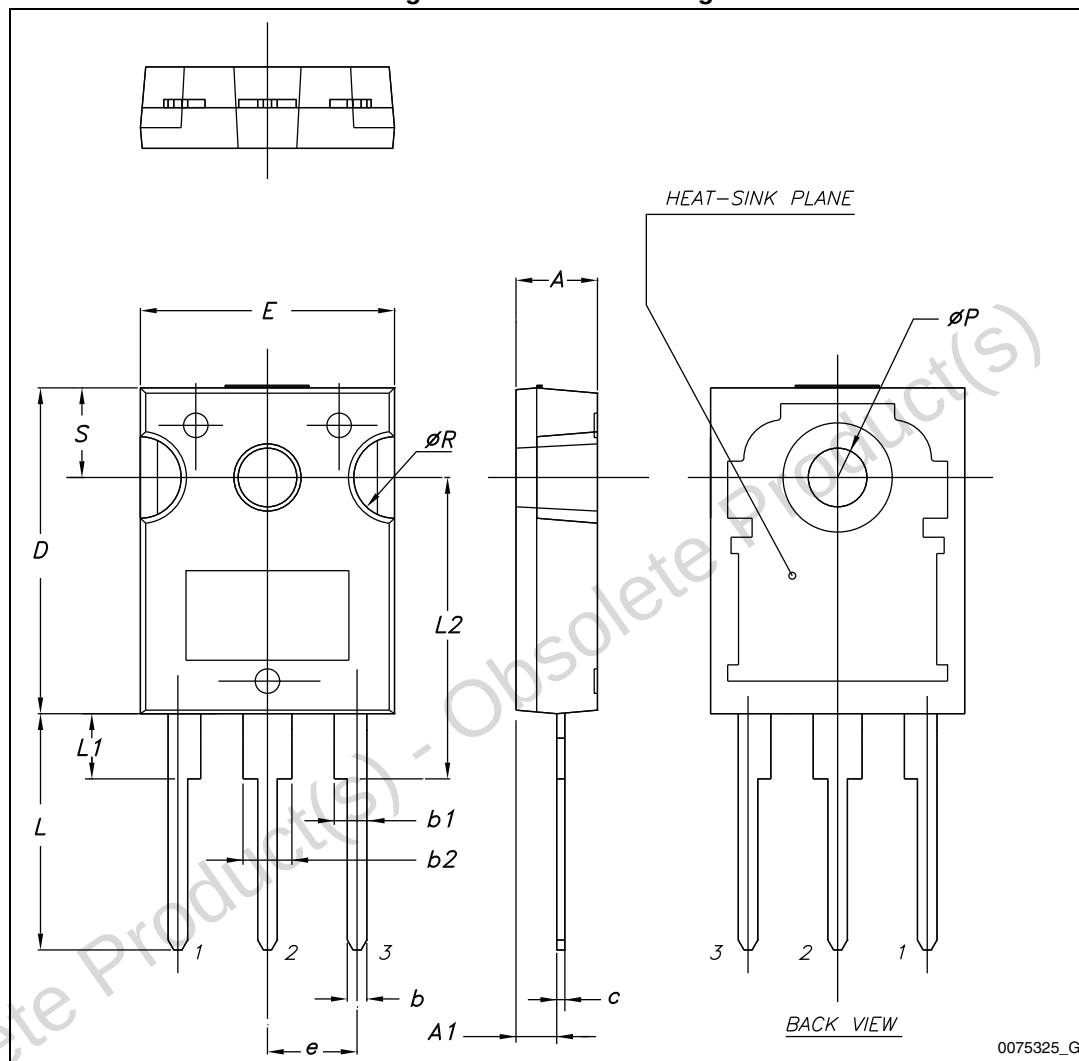


Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Revision history

Table 13. Document revision history

Date	Revision	Changes
30-Aug-2004	3	Preliminary version
17-Aug-2005	4	Complete version with curves
08-Sep-2005	5	Inserted ecopack indication
14-Oct-2005	6	New package inserted: TO-247
26-Jul-2006	7	New template, no content change
06-May-2014	8	– Updated: Figure 17, 18, 19 and 20 – Updated: Section 4: Package mechanical data – Minor text changes – The part number STP14NK60ZFP has been moved to a separate datasheet

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